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**AMENDMENTS TO THE CLAIMS:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently amended) A semiconductor device comprising: ~~a TFT containing an active layer having source and drain regions and a channel forming region being formed over a substrate~~[[,]]

a TFT formed over a substrate;

an active layer formed in the TFT;

source and drain regions formed in the active layer; and

a channel forming region formed in the active layer and between the source and drain regions.

wherein a portion of the channel forming region is convexed or concaved in a channel width direction, ~~said channel width direction being~~ which is parallel to a plane of the substrate.

2. (Currently amended) A semiconductor device comprising: ~~a TFT containing an active layer having a channel forming region formed over a substrate~~[[,]]

a TFT formed over a substrate;

an active layer formed in the TFT;

source and drain regions formed in the active layer; and

a channel forming region formed in the active layer and between the source and drain regions.

wherein a portion of the channel forming region is convexed or concaved in a channel width direction, ~~said channel width direction being~~ which is parallel to a plane of the substrate, and

wherein zero or one grain boundary is contained in the channel forming region.

3. (Currently amended) A semiconductor device comprising: ~~a TFT containing an active layer having a channel forming region formed over a substrate~~[[,]]

a TFT formed over a substrate;

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an active layer formed in the TFT;  
source and drain regions formed in the active layer; and  
a channel forming region formed in the active layer and between the source and drain regions.

wherein a portion of the channel forming region is convexed or concaved in a channel width direction, ~~said channel width direction being~~ which is parallel to a plane of the substrate, and

wherein the number of grain boundaries crossing the channel forming region in the width direction of the channel is zero or one.

4. (Withdrawn) A method of manufacturing a semiconductor device, comprising the steps of:

forming a semiconductor film over a substrate;

forming a crystalline semiconductor film by irradiating a laser light to said semiconductor film;

forming a convex portion or a concave portion in a region which is a portion of said crystalline semiconductor film and which later contains a channel forming region; and

irradiating the laser light to said crystalline semiconductor film in which the convex portion or the concave portion is formed.

5. (Withdrawn) A method of manufacturing a semiconductor device, comprising the steps of:

forming a semiconductor film over a substrate;

forming a crystalline semiconductor film by irradiating a laser light to said semiconductor film;

forming a convex portion or a concave portion in a region which is a portion of said crystalline semiconductor film and which later contains a channel forming region; and

irradiating the laser light to the top surface and to the bottom surface of said crystalline semiconductor film in which the convex portion or the concave portion is formed.

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6. (Withdrawn) A method of manufacturing a semiconductor device, comprising the steps of:

- forming a semiconductor film over a substrate;
- forming semiconductor islands by patterning said semiconductor film, each of said semiconductor island having a convex portion or a concave portion in a region which later contains a channel forming region, and
- crystallizing said semiconductor islands by irradiating a laser light.

7. (Withdrawn) A method of manufacturing a semiconductor device, comprising the steps of:

- forming a semiconductor film over a substrate;
- forming semiconductor islands by patterning said semiconductor film, each of said semiconductor island having a convex portion or a concave portion in a region which later contains a channel forming region, and
- crystallizing said semiconductor islands by irradiating a laser light to the top surface and to the bottom surface thereof.

8. (Withdrawn) The method of manufacturing a semiconductor device according to claim 5, wherein a relationship of  $0 < (I_0' / I_0) < 1$ , or a relationship of  $1 < (I_0' / I_0)$ , exists between the effective energy strength of the laser light irradiated on the top surface of said semiconductor film ( $I_0$ ) and the effective energy strength of the laser light irradiated on the bottom surface of said semiconductor film ( $I_0'$ ).

9. (Withdrawn) The method of manufacturing a semiconductor device according to claim 7, wherein a relationship of  $0 < (I_0' / I_0) < 1$ , or a relationship of  $1 < (I_0' / I_0)$ , exists between the effective energy strength of the laser light irradiated on the top surface of said semiconductor island ( $I_0'$ ) and the effective energy strength of the laser light irradiated on the bottom surface of said semiconductor island ( $I_0$ ).

10. (Previously Presented) A semiconductor device according to any one of claims 1 to 3, wherein said semiconductor device is incorporated into an electronic device selected

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from the group consisting of a personal computer, a projector, a digital camera, a video camera, a head mounted display, a portable information terminal, a navigation system, a game machine, an image playback machine and a music playback machine.

11. (Currently amended) A semiconductor device comprising:  
a semiconductor layer formed over a substrate; and  
a channel forming region and source and drain regions formed in said semiconductor layer,  
wherein said channel forming region is formed between said source and drain regions,  
wherein a portion of said channel forming region is convexed in a direction perpendicular to a channel length direction and parallel to a plane of the substrate.

12. (Currently amended) A semiconductor device comprising:  
a semiconductor layer formed over a substrate; and  
a channel forming region and source and drain regions formed in said semiconductor layer,  
wherein the channel forming region is formed between the source and drain regions,  
wherein a portion of said channel forming region is concaved in a direction perpendicular to a channel length direction and parallel to a plane of the substrate.

13. (Currently amended) A semiconductor device comprising:  
a semiconductor layer formed over a substrate; and  
a channel forming region and source and drain regions formed in said semiconductor layer,  
wherein said channel forming region is formed between said source and drain regions,  
wherein a portion of said channel forming region is convexed in a channel width direction, said channel width direction being parallel to a plane of the substrate.

14. (Currently amended) A semiconductor device comprising:  
a semiconductor layer formed over a substrate; and

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a channel forming region and source and drain regions formed in said semiconductor layer,

wherein said channel forming region is formed between said source and drain regions,

wherein a portion of said channel forming region is concaved in a channel width direction, said channel width direction being parallel to a plane of the substrate.

15. (Currently amended) A semiconductor device comprising:

a semiconductor layer formed over a substrate; and

a channel forming region and source and drain regions formed in said semiconductor layer,

wherein said channel forming region is formed between said source and drain regions,

wherein a portion of said channel forming region is convexed in a direction perpendicular to a carrier flow direction and parallel to a plane of the substrate.

16. (Currently amended) A semiconductor device comprising:

a semiconductor layer formed over a substrate; and

a channel forming region and source and drain regions formed in said semiconductor layer; [[and]]

wherein said channel forming region is formed between said source and drain regions,

wherein a portion of said channel forming region is concaved in a direction perpendicular to a carrier flow direction and parallel to a plane of the substrate.

17. (Previously Presented) A semiconductor device according to any one of claims 11-16, wherein said semiconductor device is incorporated into an electronic device selected from the group consisting of a personal computer, a projector, a digital camera, a video camera, a head mounted display, a portable information terminal, a navigation system, a game machine, an image playback machine and a music playback machine.

18. (Currently amended) A semiconductor device according to claim 1, wherein said channel width direction is perpendicular to a ~~carrier flow~~ direction in which a carrier flows from the source region to the drain region.

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19. (Currently amended) A semiconductor device according to claim 2, wherein said channel width direction is perpendicular to a ~~carrier-flow~~ direction in which a carrier flows from the source region to the drain region.

20. (Currently amended) A semiconductor device according to claim 3, wherein said channel width direction is perpendicular to a ~~carrier-flow~~ direction in which a carrier flows from the source region to the drain region.

21. (Currently amended) A semiconductor device according to claim 11, wherein said channel length direction is parallel to a ~~carrier-flow~~ direction in which a carrier flows from the source region to the drain region.

22. (Currently amended) A semiconductor device according to claim 12, wherein said channel length direction is parallel to a ~~carrier-flow~~ direction in which a carrier flows from the source region to the drain region.

23. (Currently amended) A semiconductor device according to claim 13, wherein said channel width direction is perpendicular to a ~~carrier-flow~~ direction in which a carrier flows from the source region to the drain region.

24. (Currently amended) A semiconductor device according to claim 14, wherein said channel width direction is perpendicular to a ~~carrier-flow~~ direction in which a carrier flows from the source region to the drain region.